

Silicon NPN Power Transistors

2SC4276

DESCRIPTION

- With TO-3PN package
- High voltage ,high speed
- Low collector saturation voltage
- High reliability

APPLICATIONS

- Switching regulators
- DC-DC convertor
- Solid state relay
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

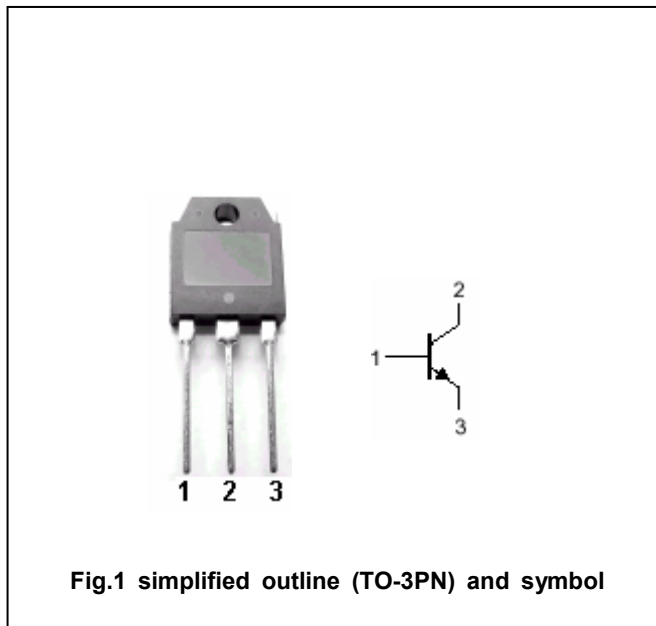


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	500	V
V _{CEO}	Collector-emitter voltage	Open base	400	V
V _{EBO}	Emitter-base voltage	Open collector	10	V
I _C	Collector current		15	A
I _B	Base current		5	A
P _C	Collector power dissipation	T _C =25□	80	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction case	1.56	□/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	10			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =6A; I _B =1.2A			0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =6A; I _B =1.2A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =450V; I _E =0			100	μA
I _{EBO}	Emitter cut-off current	V _{EB} =10V; I _C =0			100	μA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =5V	25		65	

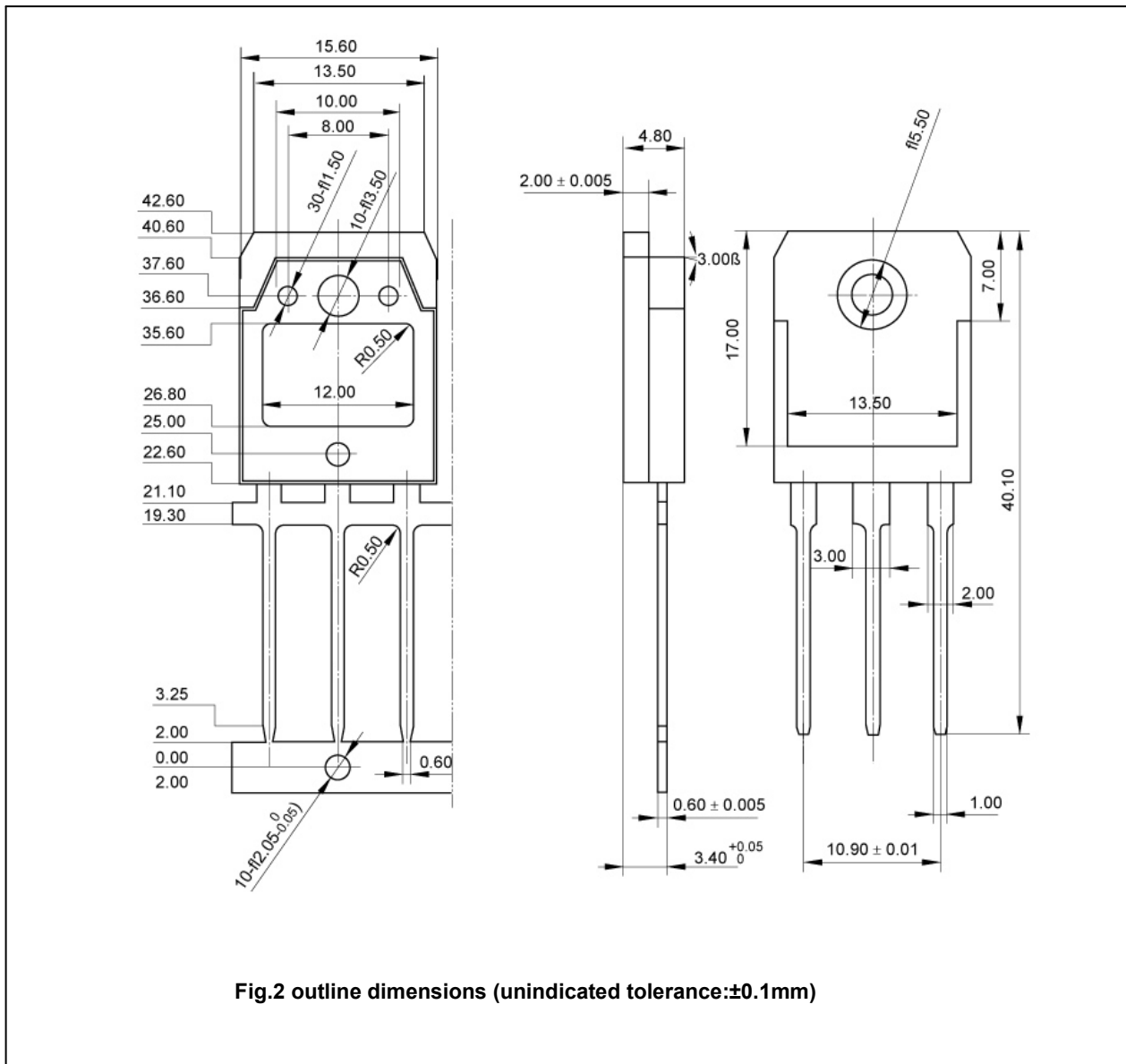
Switching times

t _{on}	Turn-on time	I _C =7.5A; R _L =20Ω I _{B1} =0.75A; I _{B2} =-1.5A P _w = 20μs; Duty≤2%			1.0	μs
t _s	Storage time				2.5	μs
t _f	Fall time				0.5	μs

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PACKAGE OUTLINE



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